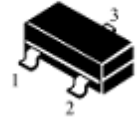




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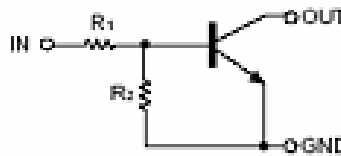
SOT-23

- 1. IN
- 2. GND
- 3. OUT



■ **DESCRIPTION&EQUIVALENT CIRCUIT** 功能和等效電路

NPN DIGITAL TRANSISTOR(BUILT-IN RESISTORS)數字晶體管(内置電阻)



■ **MAXIMUM RATINGS** 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Supply Voltage 供給電壓	V_{CC}	50	V
Input Voltage 輸入電壓	V_{IN}	-10 ~ 40	V
Output Current 輸出電流	$I_{O(MAX)}$	100	mA
Power Dissipation 耗散功率	P_D	200	mW
Junction Temperature 結溫	T_j	125	°C
Storage Temperature 儲存溫度	T_{stg}	-55 ~ +125	°C

■ **DEVICE MARKING** 打標

GMDTC114E(DTC114E)=24



GMDTC114E

■ **ELECTRICAL CHARACTERISTICS** 電特性

(**T_A=25°C unless otherwise noted** 如無特殊說明，溫度為 25°C)

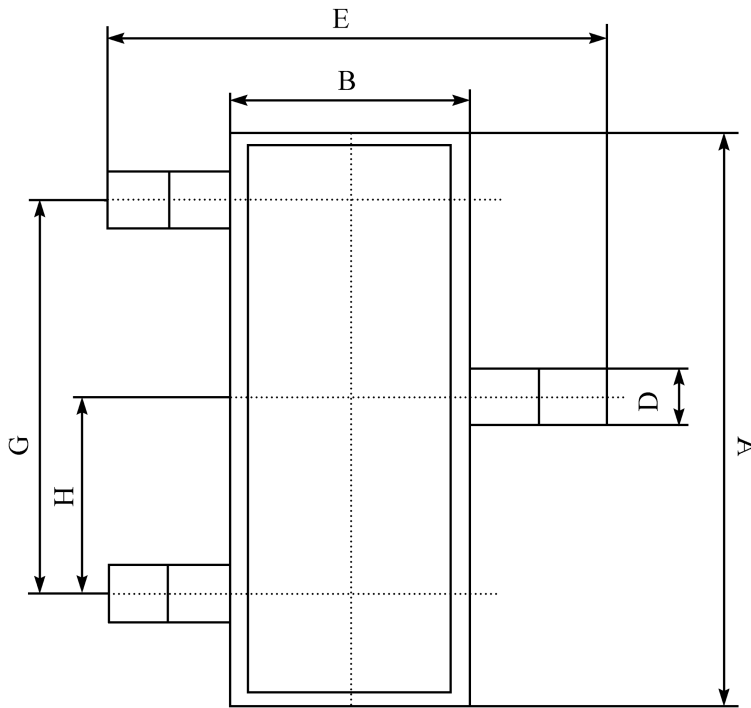
Characteristic 特性參數	Symbol 符號	Test Condition 測試條件	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Input Voltage 輸入電壓	V _{I(OFF)}	V _{CC} =5V, I _O =100uA	—	—	0.5	V
	V _{I(ON)}	V _O =0.3V, I _O =10mA	3	—	—	
Output Voltage 輸出電壓	V _{O(ON)}	I _O =10mA, I _I =0.5mA	—	—	0.3	V
Input Current 輸入電流	I _I	V _I =5V	—	—	0.88	mA
Output Current 輸出電流	I _{O(OFF)}	V _{CC} =50V, V _I =0V	—	—	0.5	uA
DC Current Gain 直流電流增益	G _I	V _O =5V, I _O =5mA	30	—	—	—
Input Resistance 輸入電阻	R _I	—	7	10	13	KΩ
Resistance Ratio 電阻比率	R ₂ /R ₁	—	0.8	1	1.2	—



GMDTC114E

■DIMENSION 外形封裝尺寸

單位(UNIT): mm



序號	數值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°

